

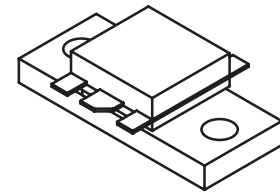
The RF Line
NPN Silicon
RF Power Transistor

Designed for 24 Volt UHF large-signal, common base amplifier applications in industrial and commercial FM equipment operating in the range of 850–960 MHz.

- Motorola Advanced Amplifier Concept Package
- Specified 24 Volt, 900 MHz Characteristics
Output Power = 60 Watts
Power Gain = 7.0 dB Min
Efficiency = 60% Min
- Double Input/Output Matched for Wideband Performance and Simplified External Matching
- Series Equivalent Large-Signal Characterization
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Silicon Nitride Passivated
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MRF898

60 W, 850–960 MHz
RF POWER
TRANSISTOR
NPN SILICON



CASE 333A-02, STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	30	Vdc
Collector–Base Voltage	V_{CBO}	55	Vdc
Emitter–Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	10	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	175 1.0	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	–65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 50 \text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 50 \text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	55	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 5.0 \text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}$, $V_{BE} = 0$, $T_C = 25^\circ\text{C}$)	I_{CES}	—	—	10	mAdc

(continued)



ARCHIVE INFORMATION

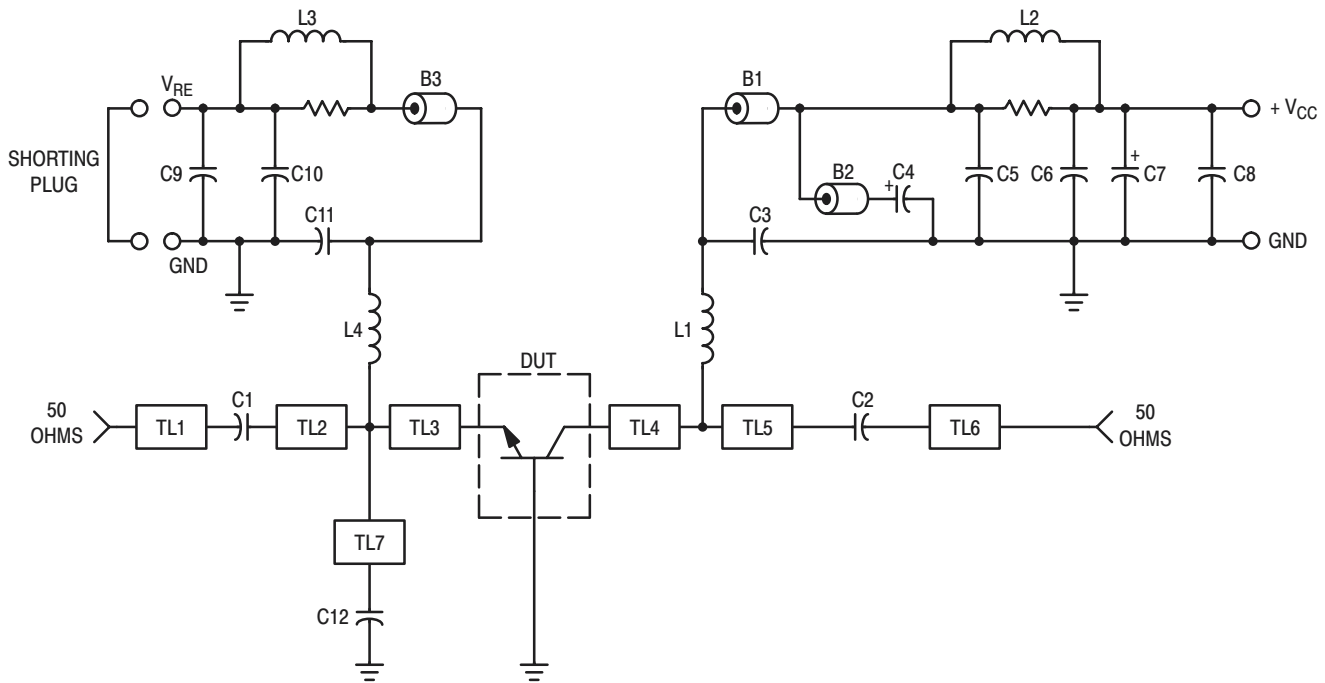
ARCHIVE INFORMATION

ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ($I_C = 2.0 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	20	50	150	—
DYNAMIC CHARACTERISTICS					
Output Capacitance (1) ($V_{CB} = 24 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{ob}	—	60	—	pF
FUNCTIONAL TESTS					
Common-Base Amplifier Power Gain ($V_{CC} = 24 \text{ Vdc}$, $P_{out} = 60 \text{ W}$, $f = 900 \text{ MHz}$)	G_{pb}	7.0	7.9	—	dB
Collector Efficiency ($V_{CC} = 24 \text{ Vdc}$, $P_{out} = 60 \text{ W}$, $f = 900 \text{ MHz}$)	η	60	65	—	%
Output Mismatch Stress ($V_{CC} = 24 \text{ Vdc}$, $P_{out} = 60 \text{ W}$, $f = 900 \text{ MHz}$, $VSWR = 5:1$, all phase angles)	ψ	No Degradation in Output Power			

NOTE:

1. Value of "C_{ob}" is that of die only. It is not measurable in MRF898 because of internal matching network.



- B1, B2, B3 — Bead, Ferroxcube 56-390-65/3B
- C1, C2, C12 — 39 pF, 100 Mil Chip Capacitor
- C3, C11 — 91 pF, Mini Underwood or Equivalent
- C4, C7, C9 — 10 μF , 35 V Electrolytic
- C5 — 4000 pF, 1.0 kV Ceramic
- C6, C10 — 1000 pF, 350 V Unelco or Equivalent
- C8 — 47 pF, 100 Mil Chip Capacitor
- L1, L4 — 4 Turns #18 AWG Choke
- L2 — 11 Turns #20 AWG Choke on 10 Ohm, 1.0 Watt Resistor
- L3 — 3 Turns #18 AWG Choke on 10 Ohm, 1.0 Watt Resistor

- TL1, TL6 — 50 Ohm Microstrip
- TL2 — 400 x 950 Mils
- TL3, TL4 — 140 x 200 Mils
- TL5 — 320 x 690 Mils
- TL7 — 260 x 230 Mils
- Board — 3M Epsilam-10, 50 Mil
- Bias Boards — 1/32" G10 or Equivalent

Figure 1. 850-960 MHz Broadband Test Circuit

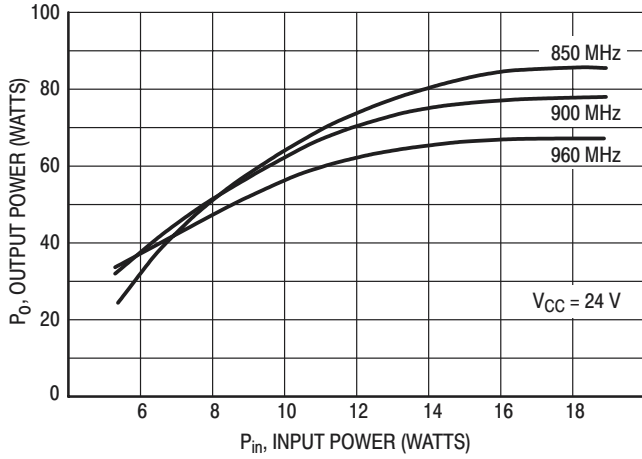


Figure 2. Output Power versus Input Power

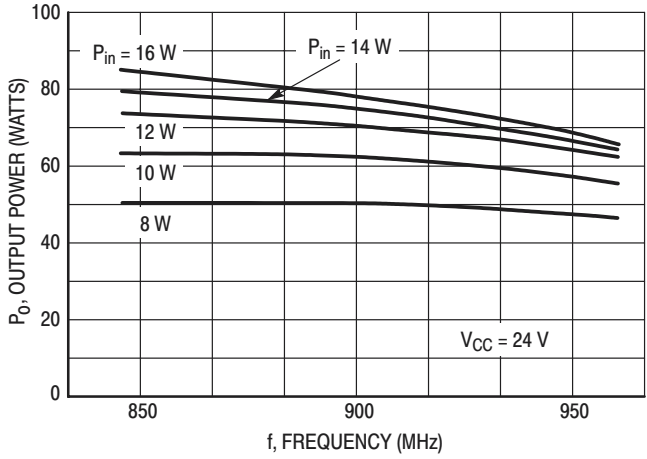


Figure 3. Output Power versus Frequency

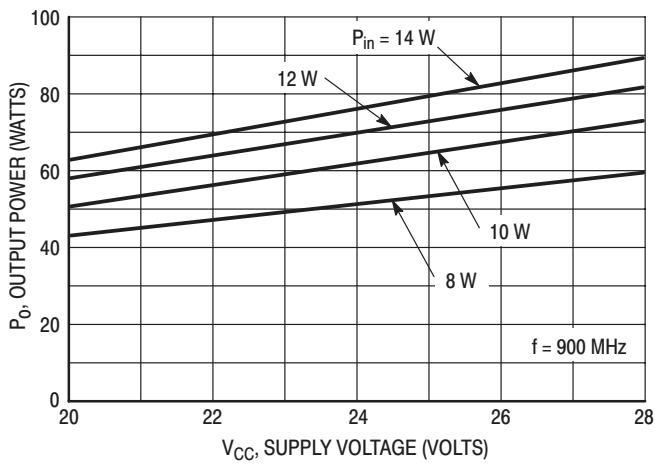


Figure 4. Output Power versus Supply Voltage

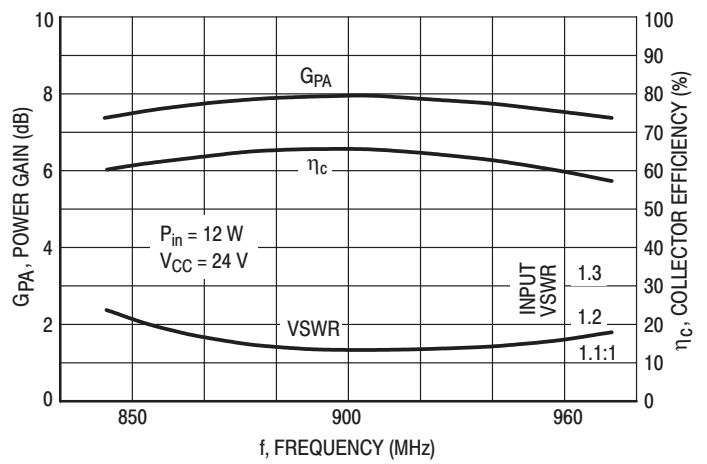


Figure 5. Typical Broadband Circuit Performance

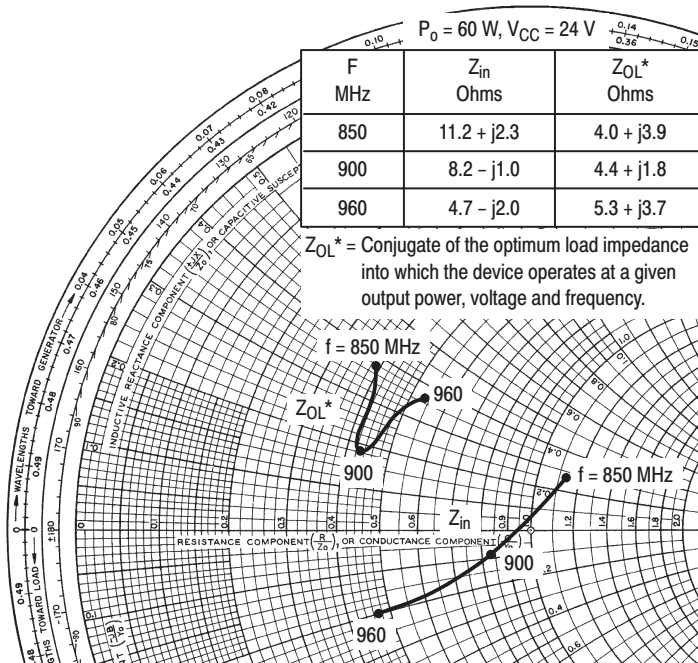
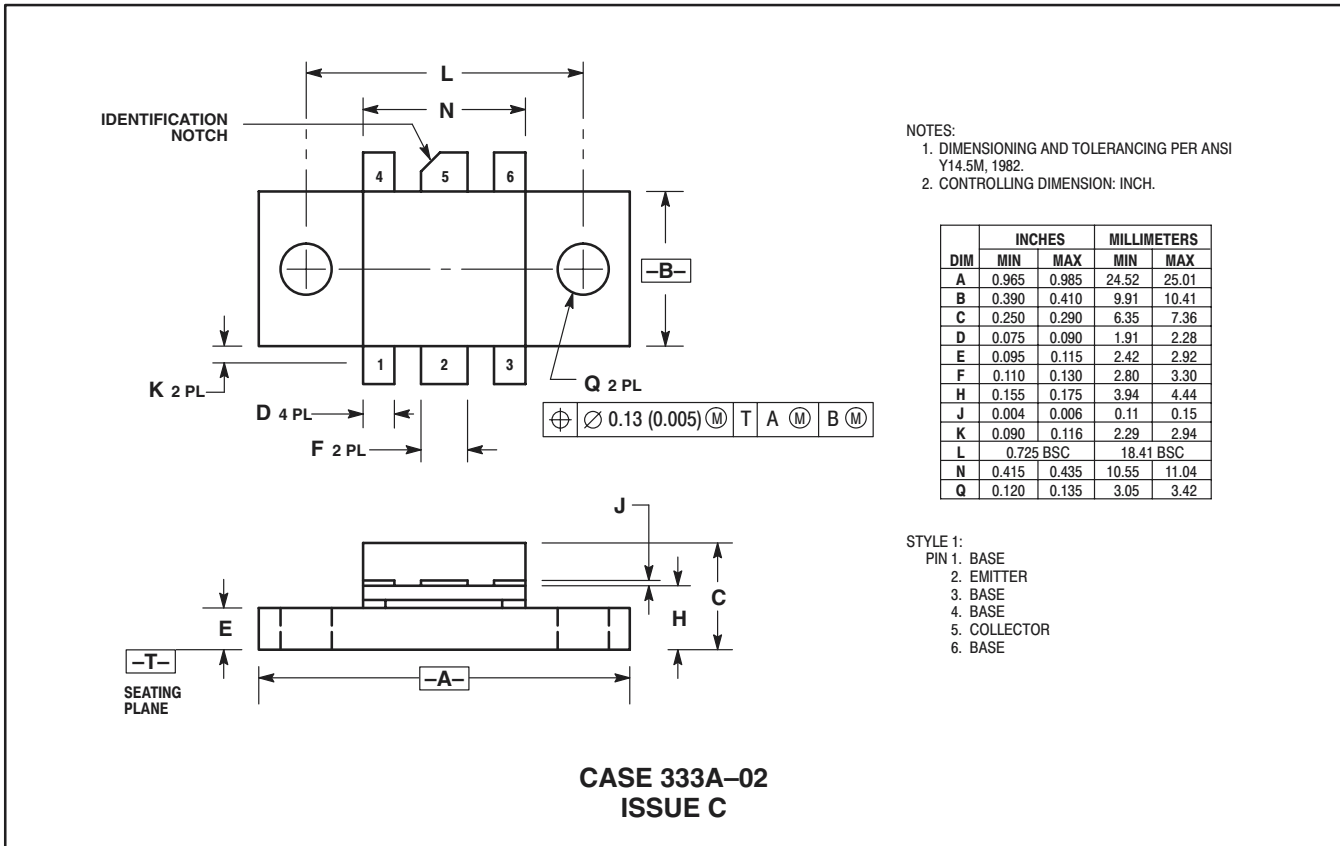


Figure 6. Input/Output Impedance versus Frequency

PACKAGE DIMENSIONS



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